

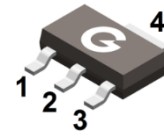
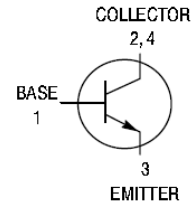
Features

- Epitaxial planar die construction
- Ideal for low power amplification and switching
- Complementary NPN type available PZT2907A

HF

Mechanical Data

- Case: SOT-223
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208



SOT-223

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
PZT2222A	SOT-223	4000 pcs / Tape & Reel	1P

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	75	V
Collector-Emitter Breakdown Voltage	V _{CEO}	40	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Collector Current (Continuous)	I _C	0.6	A
Collector Current –Peak pulse width ≤ 40μs, δ = 0.35	I _{CM}	1.5	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (Collector) *1	P _D	1.15	W
Thermal Resistance (Junction-to-Ambient)	R _{θJA}	108	°C/W
Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note1: Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm²

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	75	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60\text{V}, I_E = 0$	-	-	10	nA
Collector Cut-off Current	I_{CEX}	$V_{CE} = 60\text{V}, V_{EB(OFF)} = -3\text{V}$	-	-	10	nA
Base Cut-off Current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$	-	-	10	nA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 0.1\text{mA}$	35	-	-	-
		$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	50	-	-	-
		$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	75	-	-	-
		$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	100	-	300	-
		$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	40	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	-	0.3	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	1	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	-	1.2	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	2	V
Output Capacitance	C_{OBO}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	-	8	pF
Input Capacitance	C_{IBO}	$I_C = 0, V_{EB} = 0.5\text{V}, f = 1\text{MHz}$	-	-	25	pF
Transition Frequency	f_T	$I_C = 20\text{mA}, V_{CE} = 20\text{V}$ $f = 100\text{MHz}$	300	-	-	MHz
Delay Time	t_d	$V_{CC} = 30\text{V}$	-	-	10	ns
Rise Time	t_r	$I_C = 150\text{mA}, I_{B1} = 15\text{mA}$	-	-	25	ns
Storage Time	t_s	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$	-	-	225	ns
Fall Time	t_f	$I_{B1} = I_{B2} = 15\text{mA}$	-	-	60	ns

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

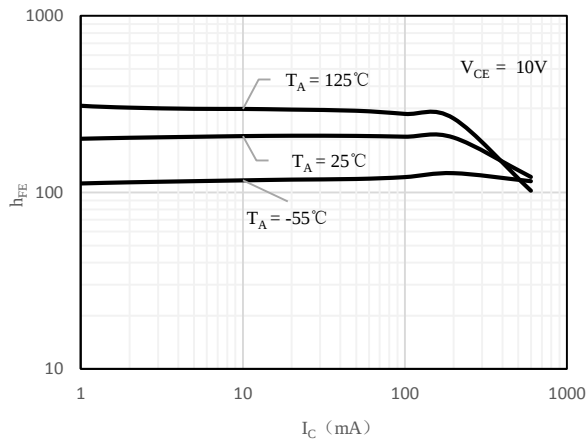


Fig 1 h_{FE} vs. I_C

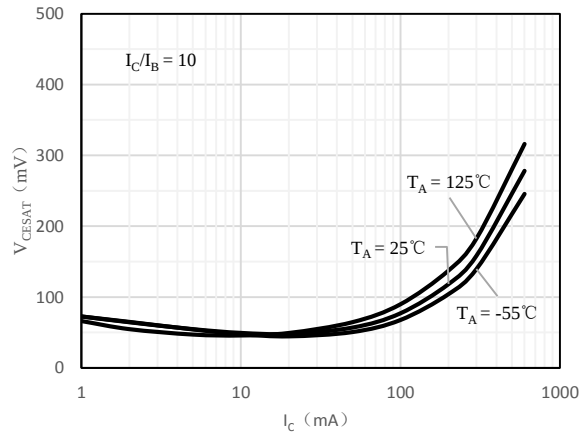


Fig 2 $V_{CE(sat)}$ vs. I_C

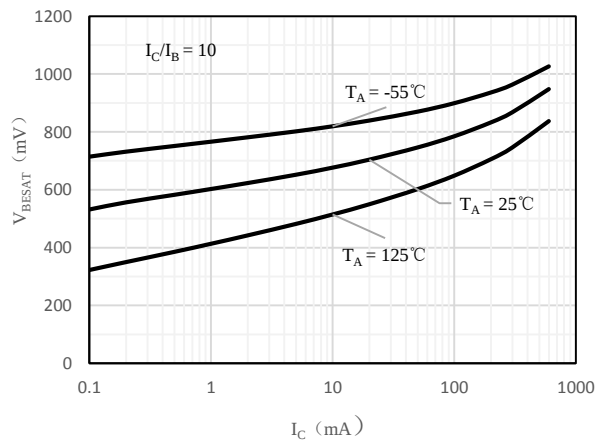


Fig 3 $V_{BE(sat)}$ vs. I_C

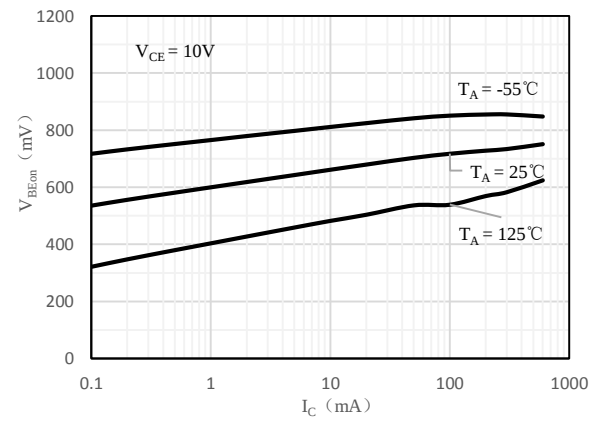
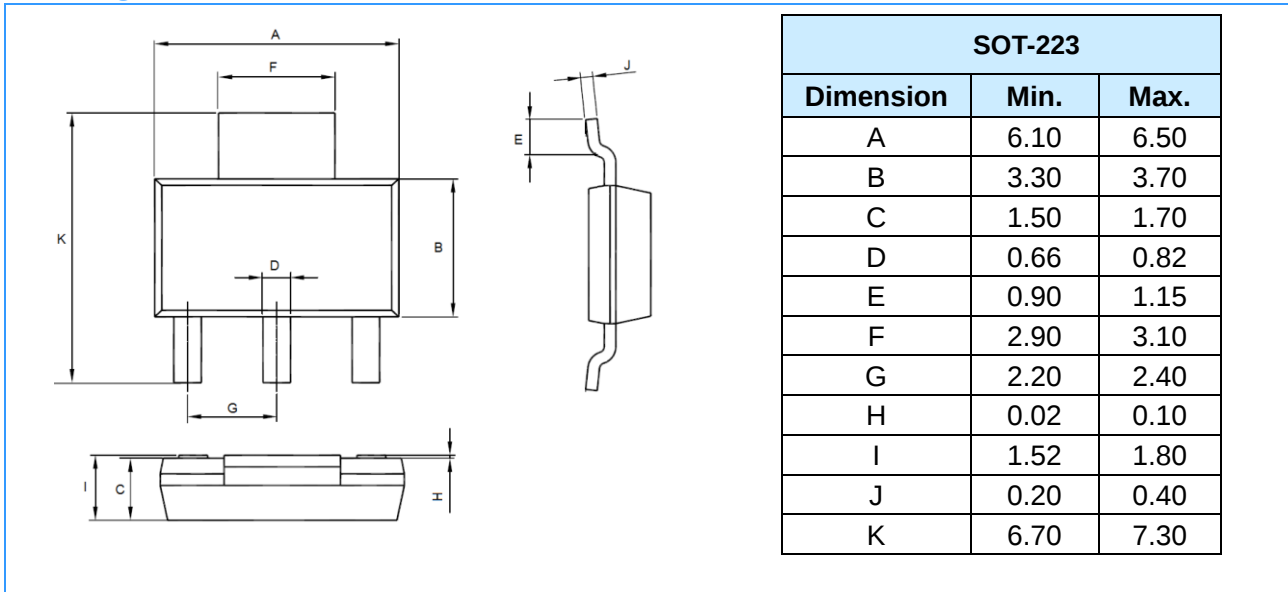
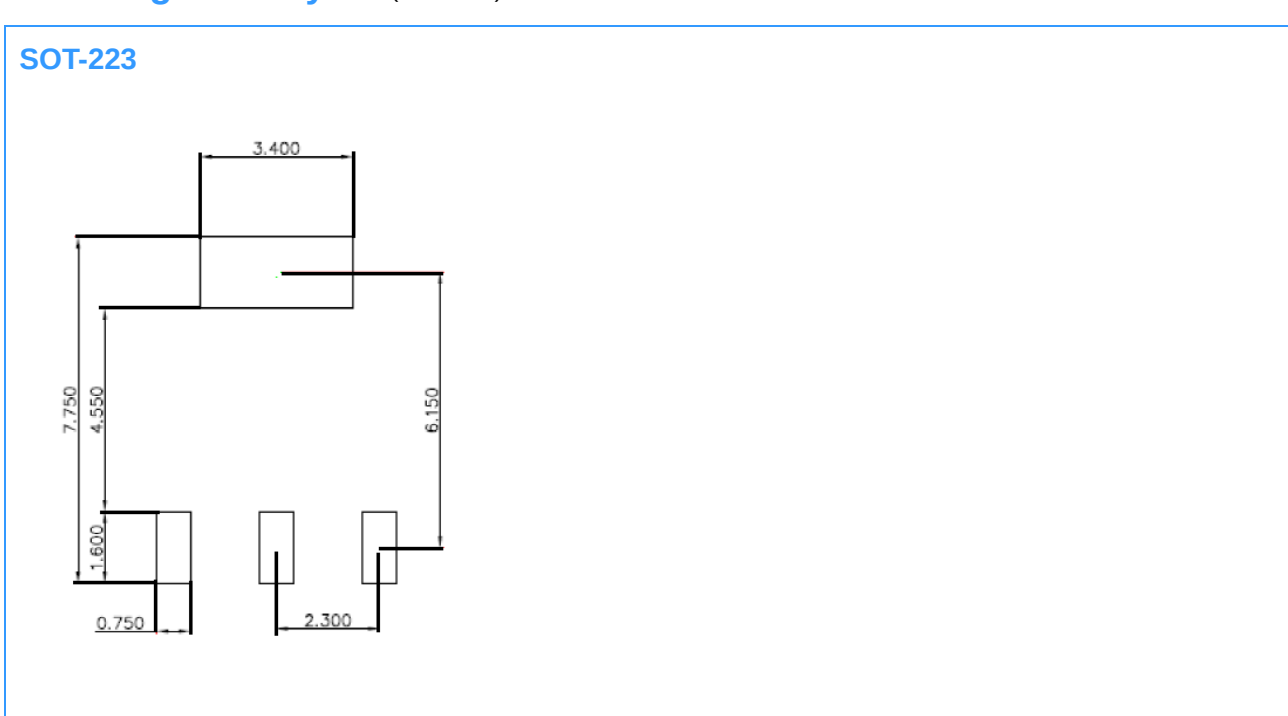


Fig 4 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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